

CLAIMS

1. A bonded wafer having a base wafer wherein a back surface of the base wafer is chemically etched, a chamfered part of the base wafer is subjected to chamfering and mirror finishing to form a mirror surface, and the chemically etched back surface is subjected to acid etching following to alkali etching.

2. A bonded wafer having a base wafer wherein a back surface of it's the base wafer is chemically etched and a chamfered part of the base wafer is subjected to chamfering and mirror finishing to form a mirror surface, and on the chemically etched back surface, a maximal depth of pits is 6 μm or less and an average value of waviness is 0.04 μm or less.

3. A bonded wafer having a base wafer wherein a power spectrum density on a back surface of the base wafer is 0.5 to 10 μm^3 as measured by waviness having a wavelength of 10 mm.

4. A bonded wafer having a base wafer wherein at least a back surface and a chamfered part of the base wafer are mirror surface and the chamfered part of the base wafer is subjected to chamfering and mirror finishing.